

AMENDMENTS TO THE CLAIMS

Claims 1-10, 16-21, 25, and 26 were pending prior to the entry of these amendments. Please amend Claims 1-3, 7-10, 16-18, 25, and 26 as indicated below. Please add new Claims 27-34 as indicated below.

1. **(Currently Amended)** A method of forming a layer of a conductive material on a wafer, wherein a seed layer coats a front surface and an edge surface of the wafer, and wherein the edge surface includes a back edge surface, a bevel surface, and a front edge surface, the method comprising ~~the steps of:~~

removing an edge portion of the seed layer from the back edge surface and the bevel surface without removing the seed layer from a central portion of the front surface and front edge surface while the central portion of the seed layer is exposed; and

forming conductive material onto the seed layer coating the front edge surface and the front surface of the wafer after removing the edge portion of the seed layer from the back edge surface and the bevel surface.

2. **(Currently Amended)** The method of Claim 1, further comprising ~~the step of~~ removing at least a part of the seed layer ~~which is on~~ from the front edge surface.

3. **(Currently Amended)** The method of Claim 1, further comprising rotating the wafer during ~~the step of removing~~ the edge portion of the seed layer.

4. (Original) The method of Claim 3, further comprising the step of applying a process solution onto the back edge surface of the wafer while it is rotated.

5. (Original) The method of Claim 1, wherein the step of removing comprises chemical etching.

6. (Original) The method of Claim 1, wherein the step of removing comprises electrochemical etching.

7. **(Currently Amended)** The method of Claim 2, further comprising rotating the wafer prior to ~~the step of removing~~ the at least a part of the seed layer from the front edge surface.

8. (**Currently Amended**) The method of Claim 7, further comprising ~~the step of~~ applying a process solution to the at least a part of the seed layer on the front edge surface while the wafer is rotated.

9. (**Currently Amended**) The method of Claim 8, wherein ~~the step of~~ removing the at least a part of the seed layer from the front edge surface comprises chemical etching.

10. (**Currently Amended**) The method of Claim 8, wherein ~~the step of~~ removing the at least a part of the seed layer from the front edge surface comprises electrochemical etching.

11.-15. (Canceled)

16. (**Currently Amended**) A method of forming a layer of a conductive material on a wafer comprising a front surface, a back surface and an edge surface, the edge surface including a back edge surface, a bevel surface, and a front edge surface, the method comprising ~~the steps of~~:

depositing a seed layer on the front surface and the edge surface of the wafer;

removing the seed layer from the back edge surface and the bevel surface while the entire seed layer is exposed; and

forming the layer by depositing the conductive material onto the seed layer coating the front edge surface and the front surface after removing the seed layer from the back edge surface and the bevel surface.

17. (**Currently Amended**) The method of Claim 16, further comprising ~~the step of~~ removing a portion of the seed layer, which is on from the front edge surface.

18. (**Currently Amended**) The method of Claim 16, further comprising rotating the wafer during ~~the step of~~ removing the seed layer from the back edge surface and the bevel surface.

19. (Original) The method of Claim 18, further comprising the step of applying a process solution to the back edge surface while the wafer is rotated.

20. (Original) The method of Claim 16, wherein the step of removing comprises electrochemical removing.

21. (Original) The method of Claim 16, wherein the step of removing comprises chemical removing.

22.-24. (Canceled)

25. **(Currently Amended)** The method of Claim 2, wherein ~~the step of removing at least part of the seed layer from the front edge surface~~ is conducted after forming the conductive material.

26. **(Currently Amended)** The method of Claim 17, wherein ~~the step of removing at least part of the seed layer from the front edge surface~~ is conducted after forming the ~~layer~~ conductive material.

27. **(New)** The method of Claim 1, wherein forming the conductive material includes contacting the seed layer on the front surface or the front edge surface of the wafer.

28. **(New)** The method of Claim 1, wherein removing the edge portion of the seed layer comprises holding the wafer with a wafer carrier and wherein forming the layer comprises holding the wafer with the wafer carrier.

29. **(New)** The method of Claim 5, wherein chemical etching comprises directing an etching solution towards the back edge of the wafer.

30. **(New)** The method of Claim 29, wherein chemical etching comprises rotating the wafer between about 250 and 550 rpm.

31. **(New)** The method of Claim 29, wherein chemical etching comprises rotating the wafer between about 150 and 350 rpm.

32. **(New)** The method of Claim 6, wherein electrochemical etching comprises contacting the wafer with porous media.

33. **(New)** The method of Claim 6, wherein electrochemical etching comprises inserting the edge of the wafer into a cavity.

34. **(New)** The method of Claim 6, wherein electrochemical etching comprises rotating the wafer.